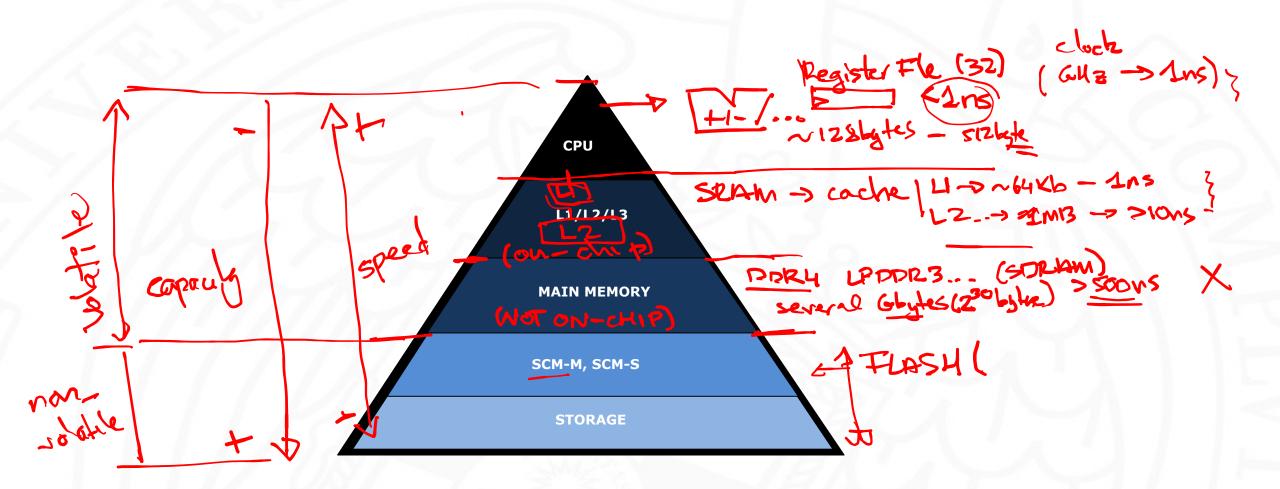


Memory and storage







Slow writes/erase

- · Fast writes en bectures read (ms)
- Very slow writes

□ Very reliable (ROM -- NOR FLASH)

- Flexible addressing
 - Random
 - Byte level

Good for code storage (instructions)

Boot, application, OS...

□ Serial and parallel interfaces (<**T**)

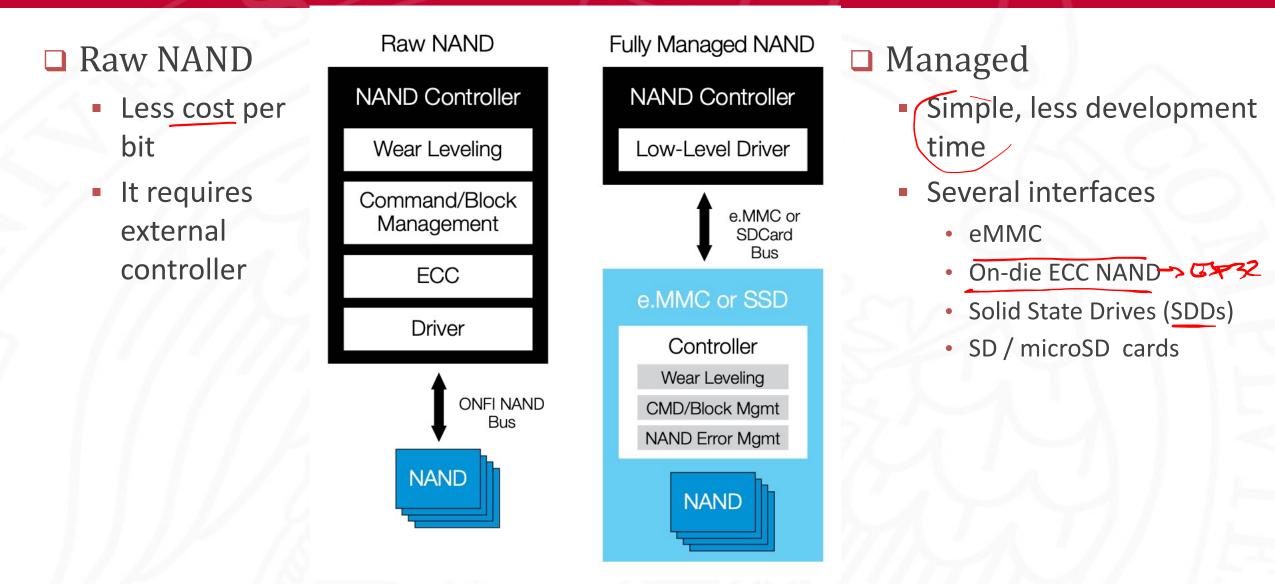
13 gte oddre sable Menorg" Str SRAM, SDEAM, To Babyle 'ot-WOR FLASH



Denser than NOR Flash

- Less area perbit
- Used to store data
 - NON random access provide. Block wise (~512 bytes pr work)
 - Writes and erase operations faster than NOR flash
 - But write operations use to include erase a whole block. Page level writing (Block > page)
- □ Many research to decrase cost/GB
 - Less lifetime: finite number of program/erase cycles per block
- □ Needs a controller
 - External or internal
 - Error Code Correction (ECC), manage damage blocks, <u>wear leveling</u> (frying to use blodes ensity alternatives
- Density alternatives
 (LC)- MLC TLC- QLC good balance performance / density
 - 3D TLC / 3D QLC are the most competitive

COMPLUTENSE Raw vs managed NAND Flash



Fuente: https://www.micron.com/products/nand-flash/choosing-the-right-nand



MPLUTENSE NAND Flash comparative

NAND Relative Attributes					
Device	(lifetime)	ECC Compatibility	Performance	Price/GB	Interface Complexity
SLC NAND	•••••	•	<u></u>	\$\$\$\$	••
Serial (SPI) NAND 5-2-32	••••	•	••••	\$\$\$\$	G
Enterprise NAND – MLC ¹	•••	••••	•	\$\$\$	••••
MLC NAND	•••	••	•••	\$\$\$	•••
TLC NAND	•	•••	\bigcirc	\$	•••
QLC NAND		•••		\$	•••
MCPs — NAND with LPDRAM	•••	•	•••	\$\$\$	••
e.MMC/UFS	••	None	••	\$\$	•
eMCP — e.MMC with LPDRAM	••	None	••	\$\$\$	•
Embedded USB (eUSB)	••••	None ²	•••	\$\$\$\$	•
SSD	••••	None	•••	\$\$\$\$	•
SD and microSD cards	••	None	••	\$	•

Fuente: https://www.micron.com/products/nand-flash/choosing-the-right-nand